NEC

SILICON POWER TRANSISTOR
2SA1010

PNP SILICON EPITAXIAL TRANSISTOR
FOR HIGH-VOLTAGE HIGH-SPEED SWITCHING

The 2SA1010 is a mold power transistor developed for high-voltage high-speed switching, and is ideal for use as a driver in devices such as switching regulators, DC/DC converters, and high-frequency power amplifiers.

FEATURES

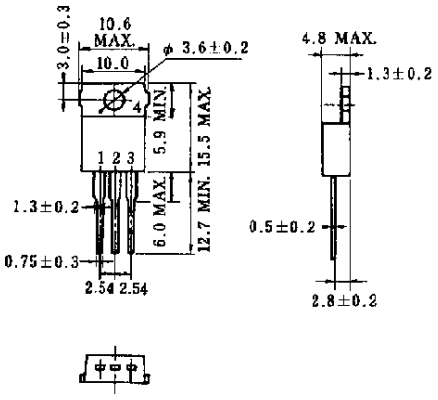
- Low collector saturation voltage
- Fast switching speed
- Complementary transistor: 2SC2334

ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	−100	V
Collector to emitter voltage	V_{CEO}	−100	V
Emitter to base voltage	V_{EBO}	−7.0	V
Collector current (DC)	$I_{C(DC)}$	−7.0	A
Collector current (pulse)	$I_{C(pulse)}$*	−15	A
Base current (DC)	$I_{B(DC)}$	−3.5	A
Total power dissipation	P_T (Tc = 25 °C)	40	W
Total power dissipation	P_T (Ta = 25 °C)	1.5	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	−55 to +150	°C

* PW ≤ 300 μs, duty cycle ≤ 10%

PACKAGE DRAWING (UNIT: mm)



Pin Connection

1. Base
2. Collector
3. Emitter
4. Fin (Collector)

EIAJ : SC-46
JEDEC : TO-220AB
IEC : —

Document No. D16118EJ2V0DS00
Date Published April 2002 N CP(K)
Printed in Japan